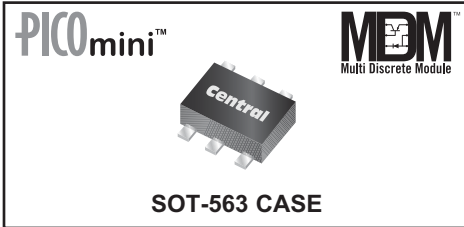


CMLM0205
MULTI DISCRETE MODULE™
SURFACE MOUNT
N-CHANNEL MOSFET AND
LOW V_F SILICON SCHOTTKY DIODE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMLM0205 is a Multi Discrete Module™ consisting of a single N-Channel MOSFET and a Low V_F Schottky diode packaged in a space saving PICOmini™ SOT-563 case. This device is designed for small signal general purpose applications where size and operational efficiency are prime requirements.

- Combination: N-Channel MOSFET and Low V_F Schottky Diode.

MARKING CODE: C25

MAXIMUM RATINGS - CASE: (T_A=25°C)

Power Dissipation	
Operating and Storage Junction Temperature	
Thermal Resistance	

SYMBOL		UNITS
P _D	350	mW
T _J , T _{stg}	-65 to +150	°C
θ _{JA}	357	°C/W

MAXIMUM RATINGS - Q1: (T_A=25°C)

Drain-Source Voltage	
Drain-Gate Voltage	
Gate-Source Voltage	
Continuous Drain Current	
Continuous Source Current (Body Diode)	
Maximum Pulsed Drain Current	
Maximum Pulsed Source Current	

SYMBOL		UNITS
V _{DS}	60	V
V _{DG}	60	V
V _{GS}	40	V
I _D	280	mA
I _S	280	mA
I _{DM}	1.5	A
I _{SM}	1.5	A

MAXIMUM RATINGS - D1: (T_A=25°C)

Peak Repetitive Reverse Voltage	
Continuous Forward Current	
Peak Repetitive Forward Current, t _p ≤1.0ms	
Peak Forward Surge Current, t _p =8.0ms	

SYMBOL		UNITS
V _{RRM}	40	V
I _F	500	mA
I _{FRM}	3.5	A
I _{FSM}	10	A

ELECTRICAL CHARACTERISTICS - Q1: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _{GSSF} , I _{GSSR}	V _{GS} =20V, V _{DS} =0		100	nA
I _{DSS}	V _{DS} =60V, V _{GS} =0		1.0	μA
I _{DSS}	V _{DS} =60V, V _{GS} =0, T _J =125°C		500	μA
I _{D(ON)}	V _{GS} =10V, V _{DS} =10V	500		mA
BV _{DSS}	V _{GS} =0, I _D =10μA	60		V
V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.0	2.5	V
V _{DS(ON)}	V _{GS} =10V, I _D =500mA		1.0	V
V _{DS(ON)}	V _{GS} =5.0V, I _D =50mA		0.15	V
V _{SD}	V _{GS} =0, I _S =400mA		1.2	V
r _{DS(ON)}	V _{GS} =10V, I _D =500mA		2.0	Ω
r _{DS(ON)}	V _{GS} =10V, I _D =500mA, T _J =125°C		3.5	Ω

R1 (18-January 2010)

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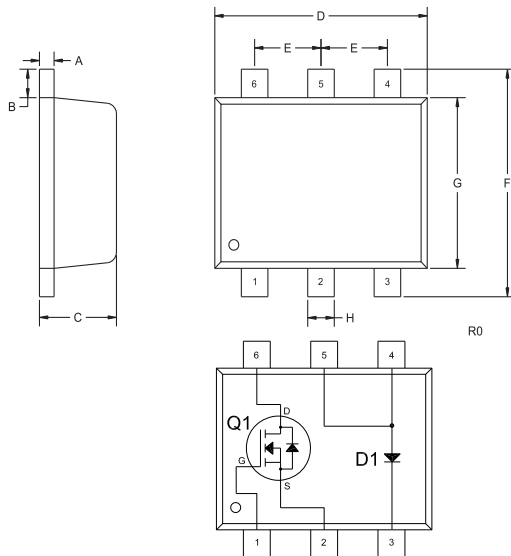
ELECTRICAL CHARACTERISTICS - Q1 - Continued:

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
r _{DS(ON)}	V _{GS} =5.0V, I _D =50mA		3.0	Ω
r _{DS(ON)}	V _{GS} =5.0V, I _D =50mA, T _J =125°C		5.0	Ω
g _{FS}	V _{DS} =10V, I _D =200mA	80		mS
C _{rSS}	V _{DS} =25V, V _{GS} =0, f=1.0MHz		5.0	pF
C _{iSS}	V _{DS} =25V, V _{GS} =0, f=1.0MHz		50	pF
C _{oss}	V _{DS} =25V, V _{GS} =0, f=1.0MHz		25	pF
t _{on} / t _{off}	V _{DD} =30V, V _{GS} =10V, I _D =200mA R _G =25Ω, R _L =150Ω		20	ns

ELECTRICAL CHARACTERISTICS - D1: (T_A=25°C)

I _R	V _R =10V		20	μA
I _R	V _R =30V		100	μA
BV _R	I _R =500μA	40		V
V _F	I _F =100μA		0.13	V
V _F	I _F =1.0mA		0.21	V
V _F	I _F =10mA		0.27	V
V _F	I _F =100mA		0.35	V
V _F	I _F =500mA		0.47	V
C _T	V _R =1.0V, f=1.0MHz		50	pF

SOT-563 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.10	0.18
B	0.008		0.20	
C	0.022	0.024	0.56	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.061	0.067	1.55	1.70
G	0.047		1.20	
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R0)

LEAD CODE:

- 1) Gate Q1
- 2) Source Q1
- 3) Cathode D1
- 4) Anode D1
- 5) Anode D1
- 6) Drain Q1

MARKING CODE: C25

R1 (18-January 2010)